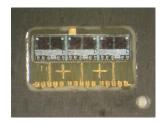
Optical Comparator Array

OPR5011

Features: • Precise active area location

- Surface mountable
- TTL compatible output
- Wide supply voltage range
- Wide operating temperature range





Description:

Each **OPR5011** device is a hybrid sensor array that consists of three channels of the OPTEK differential optical comparator ('TRI-DOC") IC. The single chip construction ensures very tight dimensional tolerances between active areas.

Specifically designed for high-speed/high-resolution encoder applications, the open collector output switches based on the comparison of the input photodiode's light current levels. Logarithmic amplification of the input signals facilitates operation over a wide range of light levels.

The surface-mountable opaque polyimide package shields the photodiodes from stray light and can withstand multiple exposures to the most demanding soldering conditions, while the gold-plated wraparound contacts provide exceptional storage and wetting characteristics.

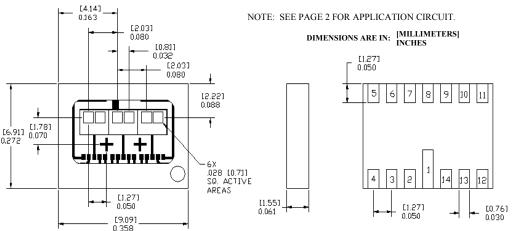
See Application Bulletin 237 for handling instructions.

Applications:

- High-speed applications
- High-resolution applications
- Applications requiring a wide range of light levels

Ordering Information Optical Optical Part # of Icc (mA)Typ / Hysteresis (%) Offset (%) **Packaging** Number Sensor **Elements** Max **Typical** Min / Max **Differential Optical OPR5011** 3 40.00 -40/+40 9 / 20 Chip Tray Comparator **Differential Optical OPR5011T** 3 9 / 20 40.00 -40/+40 Tape & Reel Comparator

Warning: Front Window is pressure sensitive. Do not apply pressure or high vacuum to window.









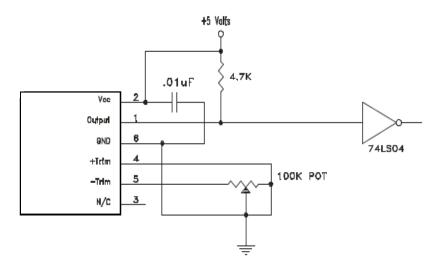
Pin#	Description	Pin #	Description	Pin #	Description	Pin#	Description
1	B - Output	5	N.C.	9	Z + Trim	13	B + Trim
2	B - Vcc	6	A - Output	10	Z -Trim	14	B -Trim
3	A + Trim	7	A - Vcc	11	Z - Output		
4	A -Trim	8	Common	12	Z - Vcc		

Optical Comparator Array

OPR5011



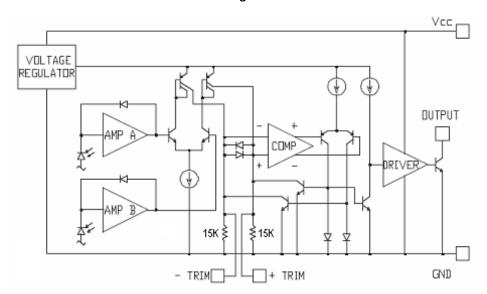
Application Circuit - OPR5011



Notes:

- (1) The 74LS04 is recommended as a means of isolating the "DOC" comparator circuitry from transients induced by inductive and capacitive loads.
- (2) It is recommended that a decoupling capacitor be placed as close as possible to the device.

Block Diagram - OPC8332



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Optical Comparator Array

OPR5011



Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)	
Storage and Operating Temperature	-40° C to +100° C
Supply Voltage	24 V
Output Voltage	24 V
Output Current	14 mA
Power Dissipation	500 mW
Solder reflow time within 5°C of peak temperature is 20 to 40 seconds ⁽¹⁾	250° C

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
I _{cc}	Supply Current	-	9	20	mA	V _{CC} = 24 V
V _{OL}	Low Level Output Voltage ⁽²⁾	-	0.3	0.4	V	I _{OL} = 14 mA, V _{CC} = 4.5 V
I _{OH}	High Level Output Current ⁽³⁾	-	0.1	1	μΑ	V _{CC} = V _O = 20 V
OPT-HYS	Optical Hysteresis ⁽⁴⁾⁽⁷⁾	-	40	-	%	V _{CC} = 5 V, I _{OL} = 1 mA
OPT-OFF	Optical Offset ⁽⁴⁾⁽⁷⁾	-40	10	+40	%	V _{CC} = 5 V, I _{OL} = 1 mA
f _{max}	Frequency Response ⁽⁵⁾	-	1	-	MHz	
t _{lh}	Output Rise Time ⁽⁶⁾	-	1	-	μs	V _{cc} = 5 V
t _{hl}	Output Fall Time ⁽⁶⁾	-	300	-	ns	

Notes:

- (1) Solder time less than 5 seconds at temperature extreme.
- (2) Pin (+) = 100.0 nW and Pin (-) = 1.0 μW .
- (3) Pin (+) = 1.0 μ W and Pin (-) = 100.0 nW.
- (4) Pin (-) is held at 1.0 μ W while Pin (+) is ramped from 0.5 μ W to 1.5 μ W and back to 0.5 μ W.
- (5) Pin (+) is modulated from $1.0~\mu W$ to $2.0~\mu W$. Pin (-) is modulated from $1.0~\mu W$ to $2.0~\mu W$ with phase shifted 180° with respect to Pin (+). Use $100~k\Omega$ trimpot to set the output signal to 50% duty cycle for maximum operating frequency.
- (6) Measured between 10% and 90% points.
- (7) Optical Hysteresis and Optical Offset are found by placing 1.0 μW of light on the inverting photodiode and ramping the light intensity of the non-inverting input from 0.5 μW up to 1.5 μW and back down. This will produce two trigger points – an upper trigger point and lower trigger point. These points are used to calculate the optical hysteresis and offset.

These are defined as:

Where:

P in (-) = Light level incident upon the "-" photodiode on the IC chip (Pin) (-) = $1.0 \mu W$).

P rise = Value of light power level incident upon the "+" photodiode that his required to switch the digital output when the

light level is an increasing level (rising edge).

P fall = Value of light power level incident upon the "+" photodiode that is required to switch the digital output when the light

level is decreasing level (falling edge).

P average = (P rise + P fall)

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